

SPTECH Silicon NPN Power Transistor

BD707

DESCRIPTION

- DC Current Gain -
: $h_{FE} = 40(\text{Min.}) @ I_C = 0.5\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = 60\text{V}(\text{Min.})$
- Complement to Type BD708

APPLICATIONS

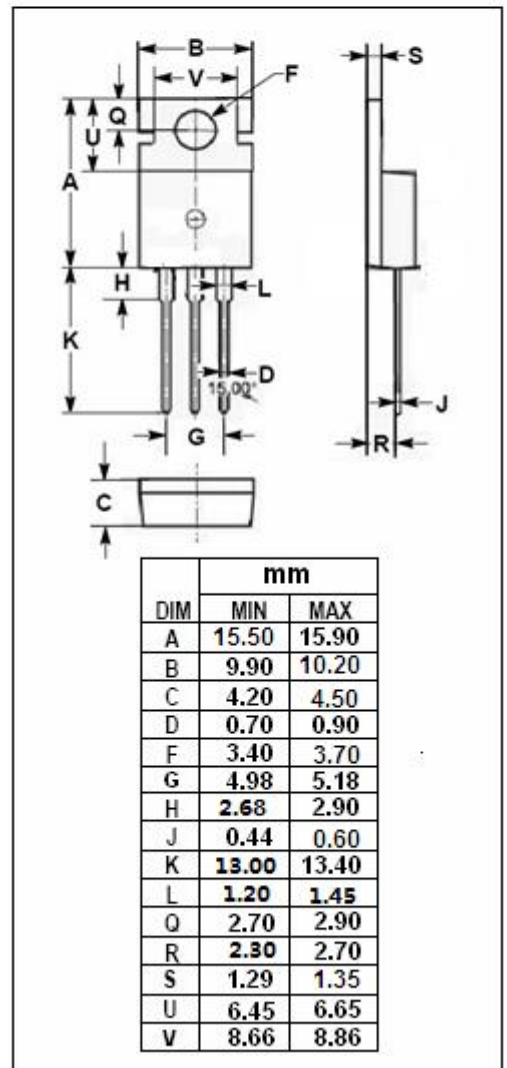
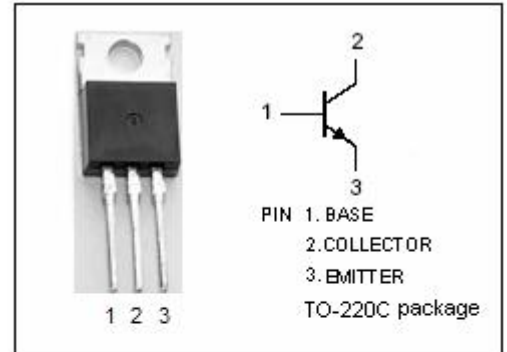
- Designed for use in power linear and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CES}	Collector-Emitter Voltage $V_{BE} = 0$	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	75	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	70	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}; I_B=0$	60		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.4\text{A}$		1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=4\text{A}; V_{CE}=4\text{V}$		1.5	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=30\text{V}; I_B=0$		1.0	mA
I_{CBO}	Collector Cutoff Current	$V_{CB}=60\text{V}; I_E=0$ $V_{CB}=60\text{V}; I_E=0; T_C=150^{\circ}\text{C}$		0.1 1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$		1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=2\text{V}$	40	400	
h_{FE-2}	DC Current Gain	$I_C=2\text{A}; V_{CE}=2\text{V}$	30		
h_{FE-3}	DC Current Gain	$I_C=4\text{A}; V_{CE}=4\text{V}$	15	150	
h_{FE-4}	DC Current Gain	$I_C=10\text{A}; V_{CE}=4\text{V}$	5		
f_T	Current-Gain—Bandwidth Product	$I_C=0.3\text{A}; V_{CE}=3\text{V}$	3		MHz